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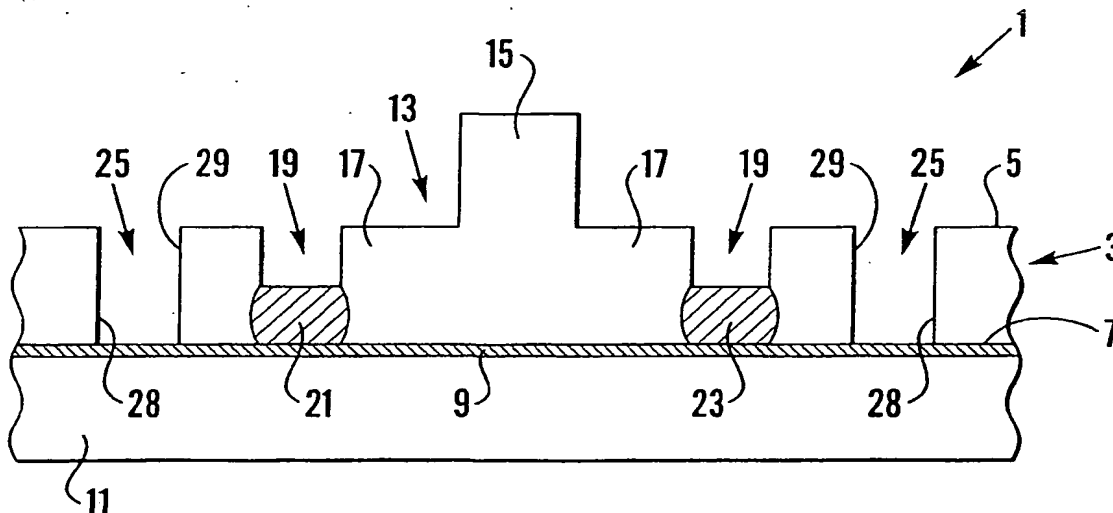
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(54) Title: SEMICONDUCTOR OPTICAL WAVEGUIDE DEVICE



(57) Abstract: A semiconductor optical waveguide device (1) comprising a semiconductor layer (3) having an upper surface (5), and a lower surface (7) which is defined by a lower confinement layer (9), the semiconductor layer having formed therein: (a) a waveguide (13); (b) at least one recess (19) adjacent to the waveguide (13) and extending from the upper surface (5) of the semiconductor layer (3); (c) at least one doped region (21, 23), at least part of which is situated between a said recess (19) and the lower confinement layer (9); and (d) at least one trench (25) adjacent to a said doped region (21, 23) and recess (19) and situated on an opposite side thereof to the waveguide, wherein the (or each) trench (25) extends from the upper surface of the semiconductor layer (3).



*For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.*